



Docket No.: 055071-0311

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of : Customer Number: 20277
Stephen D. HSU, et al. : Confirmation Number: 3609
Application No.: 10/705,231 : Group Art Unit: 1756
Filed: November 12, 2003 : Examiner: Not yet assigned

For: METHOD AND APPARATUS FOR PERFORMING MODEL-BASED LAYOUT
CONVERSION FOR USE WITH DIPOLE ILLUMINATION

INFORMATION DISCLOSURE STATEMENT

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

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Respectfully submitted,

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SHEET 1 OF 1

INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)				ATTY. DOCKET NO. 055071-0311	SERIAL NO. 10/705,231	
				APPLICANT Stephen D. HSU, et al.		
				FILING DATE November 12, 2003	GROUP 1756	
U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ₂ (<i>if known</i>)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
	US	6,553,562 B2	4-22-2003	Capodieci et al.		
	US	2004/0003368 A1	1-1-2004	Hsu et al.		
	US	2004/0139418 A1	7-15-2004	Shi et al.		
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FOREIGN PATENT DOCUMENTS						
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Code ₃ -Number 4-Kind Codes (<i>if known</i>)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation Yes No
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)						
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.				
		EURLINGS et al., "0.11 μm imaging in KrF lithography using dipole illumination", <i>Lithography for Semiconductor Manufacturing II</i> , Proceedings of SPIE, Vol. 4404 (2001) pp. 266-278				
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		TORRES et al., "Model-assisted double dipole decomposition", Proceedings of The SPIE, Bellingham, VA, vol. 4691, 3-5-2002, pp. 407-417, XP 002257323				
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		NAM, "Patterning 220nm Pitch DRAM Patterns by Using Double Mask Exposure", Proceedings of SPIE, vol. 4000, (March, 2000), pp.283-292				
		FINDERS et al., "Can DUV take us below 100 nm?" Proceedings of SPIE, vol. 4346, (2000), pp. 153-165				
		KIM et al., "Feasibility Study of Printing Sub 100 nm with ArF Lithography", Proceedings of SPIE, vol. 4346, (2000), pp. 214-221				
EXAMINER			DATE CONSIDERED			

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.